



BDY23 – 180T2

BDY24 – 181T2

BDY25 – 182T2

NPN SILICON TRANSISTORS, DIFFUSED MESA

They are NPN transistors mounted in Jedec TO-3.

LF Large Signal Power Amplification.

High Current Fast Switching.

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V _{CEO}	Collector-Emitter Voltage	BDY23, 180T2	60	V
		BDY24, 181T2	90	
		BDY25, 182T2	140	
V _{CBO}	Collector-Base Voltage	BDY23, 180T2	60	V
		BDY24, 181T2	100	
		BDY25, 182T2	200	
V _{EBO}	Emitter-Base Voltage	BDY23, 180T2 BDY24, 181T2 BDY25, 182T2	10	V
I _C	Collector Current	BDY23, 180T2 BDY24, 181T2 BDY25, 182T2	6	A
I _B	Base Current	BDY23, 180T2 BDY24, 181T2 BDY25, 181T2	3	A
P _{TOT}	Power Dissipation	@ T _C = 25°	87.5	Watts
T _J	Junction Temperature		-65 to +200	°C
T _S	Storage Temperature			

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	2	°C/W

BDY23 – 180T2

BDY24 – 181T2

BDY25 – 182T2

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit
$V_{CEO(BR)}$	Collector-Emitter Breakdown Voltage (*)	$I_C=50\text{ mA}$ $I_B=0$	BDY23, 180T2	60	-	-	V
			BDY24, 181T2	80	-	-	
			BDY25, 182T2	140	-	-	
I_{CEO}	Collector-Emitter Cutoff Current	$V_{CE}=60\text{ V}$	BDY23	-	-	1.0	mA
		$V_{CE}=90\text{ V}$	BDY24	-	-		
		$V_{CE}=140\text{ V}$	BDY25	-	-		
I_{EBO}	Emitter-Base Cutoff Current	$V_{EB}=10\text{ V}$	BDY23, 180T2	-	-	1.0	mA
			BDY24, 181T2				
			BDY25, 182T2				
I_{CES}	Collector-Emitter Cutoff Current	$V_{CE}=60\text{ V}$ $V_{BE}=0\text{ V}$	BDY23, 180T2	-	-	0.5	mA
		$V_{CE}=100\text{ V}$ $V_{BE}=0\text{ V}$	BDY24, 181T2	-	-	1.0	
		$V_{CE}=180\text{ V}$ $V_{BE}=0\text{ V}$	BDY25, 182T2	-	-	1.0	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=2.0\text{ A}$, $I_B=0.25\text{ A}$	BDY23, 180T2	-	-	1	V
			BDY24, 181T2	-	-	0.6	
			BDY25, 182T2	-	-	0.6	
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage (*)	$I_C=3\text{ mA}$	BDY23, 180T2	60	-	-	V
			BDY24, 181T2	100	-	-	
			BDY25, 182T2	200	-	-	
$V_{BE(SAT)}$	Base-Emitter Voltage (*)	$I_C=2.0\text{ A}$, $I_B=0.25\text{ A}$	BDY23, 180T2	-	-	2.0	V
			BDY24, 181T2	-	-	1.2	
			BDY25, 182T2	-	-	1.2	
h_{21E}	Static Forward Current transfer ratio (*)	$V_{CE}=4\text{ V}$ $I_C=1\text{ A}$	A	-	55	-	-
			B	-	65	-	
			C	-	90	-	
		$V_{CE}=4\text{ V}$ $I_C=2\text{ A}$	A	15	20	45	
			B	30	45	90	
			C	75	82	100	
f_T	Transition Frequency	$V_{CE}=15\text{ V}$, $I_C=0.5\text{ A}$, $f=10\text{ MHz}$		10	-	-	MHz
$t_d + t_r$	Turn-on time	$I_C=5\text{ A}$, $I_B=1\text{ A}$		-	0.3	0.5	μs
$t_s + t_f$	Turn-off time	$I_C=5\text{ A}$, $I_{B1}=1\text{ A}$, $I_{B2}=-0.5\text{ A}$		-	0.3	0.5	μs

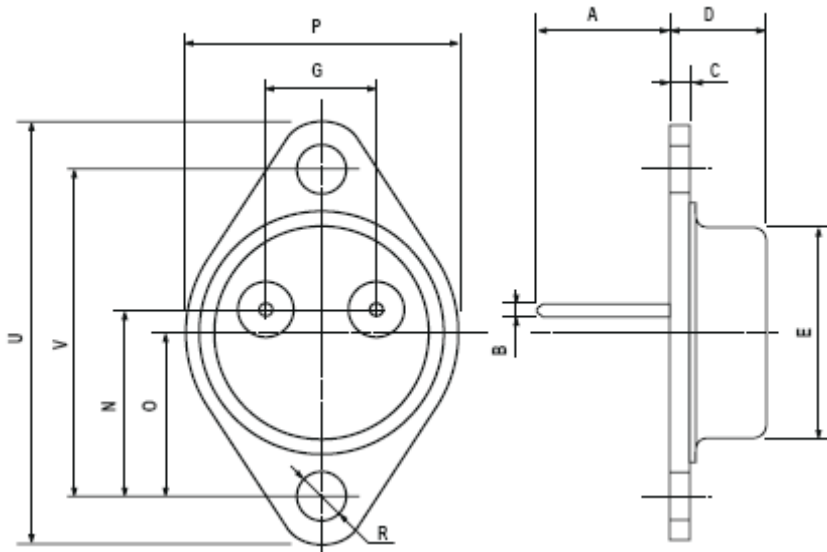
(*) Pulse Width $\approx 300\text{ }\mu\text{s}$, Duty Cycle $\angle 2.0\%$



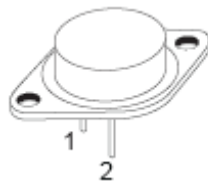
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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